

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 62-232962

(43)Date of publication of application : 13.10.1987

(51)Int.Cl.

H01L 27/14  
H04N 5/335

(21)Application number : 61-075892

(71)Applicant : SEIKO EPSON CORP

(22)Date of filing : 02.04.1986

(72)Inventor : TOGAWA EIJI

YOKOGAWA MAGOYUKI

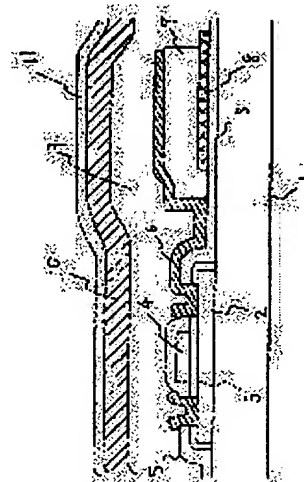
NAGAI MITSURU

## (54) SOLID-STATE IMAGE SENSING DEVICE

### (57)Abstract:

**PURPOSE:** To manufacture the title device with excellent moisture resistance by a method wherein a three layered passivation structure is composed of a high temperature cured polyimide, a low temperature cured polyimide and an inorganic material.

**CONSTITUTION:** A photodetector comprising an amorphous silicon 2 and a thin film transistor formed of a gate oxide film 3 driving the photodetector, a polycrystalline silicon gate electrode 4, interlayer insulating films 5, an aluminium electrode 6, an a-Si:H 7 and a transparent electrode 8 are formed on an insulating substrate 1 to constitute a solid image pick-up device. Furthermore, a polyimide resin coating layer 9 to be cured at the temperature not exceeding 300°C and another polyimide resin coating layer 10 to be imidized at the temperature exceeding 300°C are formed on the topmost part and after curing these two kinds of polyimide resin coating layers at the temperature exceeding 150°C and not exceeding 300°C, the other coating layer 11 comprising an inorganic material is formed at the temperature not exceeding 300°C to provide a three layered passivation layer.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office